LM805ESDCP18-0.22x0.36

Features

- 1-Channel Bi-directional ESD diode
- Low Operating Voltage: 5V
- Ultra Low Leakage: nA Level
- Low Clamping Voltage
- Response time is typically < 1 ns
- RoHS compliant
- Ultra Small Die Size, suitable for DFN1006 or SOD-323 package
- Complies with IEC 61000-4-2 standards:

  Air discharge: ±30kV

  Contact discharge: ±30kV

Die Top-View

Circuit Diagram

Wafer Information

Item	Description
Wafer size	8 inch
Wafer thickness	150±10μm
Die Size (Include scribe lane)	220μm x 360μm
Bond Pad Opening	150μm x 290μm
Scribe lane width	50μm
Gross die per wafer	370, 000 dies
Top metal for wire bond	4μm AlSiCu
Back side metal	TiNiAg

Absolute Maximum Ratings (TA=25℃ unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	P_{pk}	200	W
ESD per IEC61000-4-2 (Air) ESD per IEC61000-4-2 (Contact)	V_{ESD}	±30 ±30	kV
Operating Temperature Range	T_J	-55 to +125	℃
Storage Temperature Range	T_{stg}	-55 to +150	℃

Electrical Characteristics (TA=25℃ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			5.0	V	
Breakdown Voltage	V_{BR}	6.0	6.8	8.0	V	I_T=1mA
Leakage Current	I_{Leak}			200	nA	V_{RWM}=5V
Clamping Voltage	V_C			6.5	V	I_{PP}=1A,Tp=8/20μs
Clamping Voltage	V_C		10.0	12.0	V	I_{PP}=18A,Tp=8/20μs
Junction Capacitance	C_J		30	50	pF	V_R=0V, f=1MHz

Note: Electrical parameters are only for die, performance may alter after assembly.

NOTICE

Leiditech reserves the right to make modifications,enhancements,improvements,corrections or other changes without further notice to any product herein. Leiditech does not assume any liability arising out of the application or use of any product described herein.

Shanghai Leiditech Electronic Technology Co., Ltd.
Email: sale1@leiditech.com
Tel : +86- 021 50828806
Fax : +86- 021 50477059